

INFORMATION DISCLOSURE STATEMENT PTO-1449	Atty. Docket No. 011227	Serial No. New Appln.
	Applicant(s): Koki MUKAI	
	Filing Date: October 17, 2001	Group Art Unit: 2828

J0821 U.S. PTO
 09/078207
 10/17/01




U.S. PATENT DOCUMENTS

Examiner Initial	Document No.	Name	Date	Class	Subclass	Filing Date (If appropriate)
_____	AA					
_____	AB					
_____	AC					
_____	AD					
_____	AE					

FOREIGN PATENT DOCUMENTS

Document No.	Date	Country	Translation (Yes or No)
_____	AF		
_____	AG		
_____	AH		

OTHER DOCUMENTS

	AI	T. FUKUI, et al., GaAs Tetrahedral Quantum Dot Structure Fabricated using Selective Area Metalorganic Chemical Vapor Deposition, App. Phys. Letter 58(18), May 6, 1991, pp. 2018-2020
	AJ	S.K. Mathis, et al., Strain Relaxation of InGaAs by Lateral Oxidation of AIAs, J. Vac. Sci. Technol. B18(4), June/August 2000, pp. 2066-2071
Examiner 		Date Considered 8/06/07